



## PNP SILICON POWER TRANSISTOR

### DESCRIPTION

These 2N6317 and 2N6318 devices are an excellent choice for un-tuned amplifier applications. It is also ideal for general purpose power switch and amplifier applications. Microsemi also offers numerous other products to meet higher and lower power voltage regulation applications.



**TO-213AA (TO-66)  
Package**

**Important:** For the latest information, visit our website <http://www.microsemi.com>.

### FEATURES

- Hermetically sealed.
- Complimentary pairing with the NPN 2N6315 and 2N6316.
- RoHS compliant versions available.

### APPLICATIONS / BENEFITS

- Convenient package.
- Mechanically rugged.
- Commercial, industrial, and military uses.

### MAXIMUM RATINGS @ 25 °C unless otherwise stated

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T <sub>J</sub> and T <sub>STG</sub>	-65 to +200	°C
Thermal Resistance Junction-to-Lead <sup>(1)</sup>	R <sub>θJL</sub>	235	°C
Collector-Base Voltage	V <sub>CBO</sub>	60 80	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60 80	V
Continuous Operating Collector Current	I <sub>C</sub>	7	A
Continuous Base Current		2	A
Total Power Dissipation <sup>(2)</sup>	P <sub>T</sub>	90	W

- NOTES:**
1. At 1/8 inch from case for 10 seconds.
  2. Derate linearly at 0.515 W/°C.

#### **MSC – Lawrence**

6 Lake Street,  
Lawrence, MA 01841  
Tel: 1-800-446-1158 or  
(978) 620-2600  
Fax: (978) 689-0803

#### **MSC – Ireland**

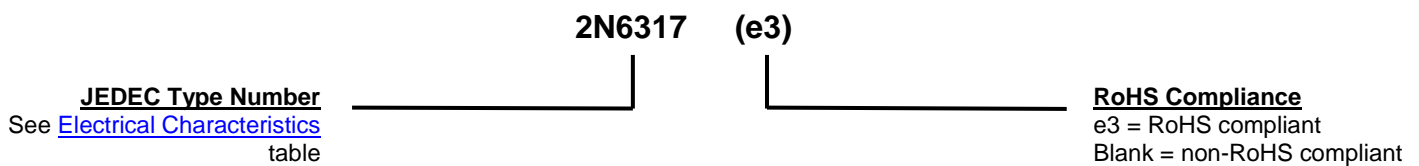
Gort Road Business Park,  
Ennis, Co. Clare, Ireland  
Tel: +353 (0) 65 6840044  
Fax: +353 (0) 65 6822298

#### **Website:**

[www.microsemi.com](http://www.microsemi.com)

**MECHANICAL and PACKAGING**

- CASE: Hermetic, TO-66 package. Nickel plate with nickel cap.
- TERMINALS: Solder dipped (Sn63/Pb37) over nickel plated alloy 52. RoHS compliant matte-tin plating is also available.
- MARKING: MSC, part number, date code, polarity symbol.
- WEIGHT: Approximately 5.7 grams.
- See [Package Dimensions](#) on last page.

**PART NOMENCLATURE**

**SYMBOLS & DEFINITIONS**

Symbol	Definition
$I_B$	Base current
$T_C$	Case temperature
$V_{CB}$	Collector-base voltage
$V_{CC}$	Collector-supply voltage
$V_{EB}$	Emitter-base voltage

**ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise stated**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
<b>STATIC CHARACTERISTICS</b>				
Collector Cutoff Current $V_{CE} = 60 V, V_{BE} = 1.5 V, T_C = 150 ^\circ C$ $V_{CE} = 80 V, V_{BE} = 1.5 V, T_C = 150 ^\circ C$	2N6317 2N6318	$I_{CEX}$	2.0	mA
Collector Cutoff Current $V_{CE} = 60 V, V_{BE} = 1.5 V$ $V_{CE} = 80 V, V_{BE} = 1.5 V$	2N6317 2N6318	$I_{CEX}$	0.25	mA
Emitter Cutoff Current $V_{EB} = 5 V$		$I_{EBO}$	1.0	mA
Collector-Emitter Open Base Sustain Voltage <sup>(1)</sup> $I_B = 0, I_C = 100 mA$	2N6317 2N6318	$V_{CEO(sus)}$	60 80	
Collector Cutoff Current, Base Open $I_B = 0, V_{CE} = 30 V$ $I_B = 0, V_{CE} = 40 V$	2N6317 2N6318	$I_{CEO}$	0.5	mA
DC Forward Current Transfer Ratio <sup>(1)</sup> $I_C = 7 A, V_{CE} = 4 V$ $I_C = 2.5 A, V_{CE} = 4 V$ $I_C = 0.5 A, V_{CE} = 4 V$		$h_{FE}$	4 25 35	125
Collector-Emitter Saturation Voltage <sup>(1)</sup> $I_C = 7.0 A, I_B = 1.75 A$ $I_C = 4.0 A, I_B = 0.4 A$		$V_{CE(sat)}$	2.0 1.0	V
Base-Emitter Saturation Voltage <sup>(1)</sup> $I_C = 7.0 A, I_B = 1.75 A$		$V_{BE(sat)}$	2.5	V
Base-Emitter Voltage <sup>(1)</sup> $I_C = 2.5 A, V_{CE} = 4.0 V$		$V_{BE}$	1.5	V

**NOTE:** 1. Pulse Width  $\leq 300 \mu s$ ; duty cycle  $\leq 2 \%$ .

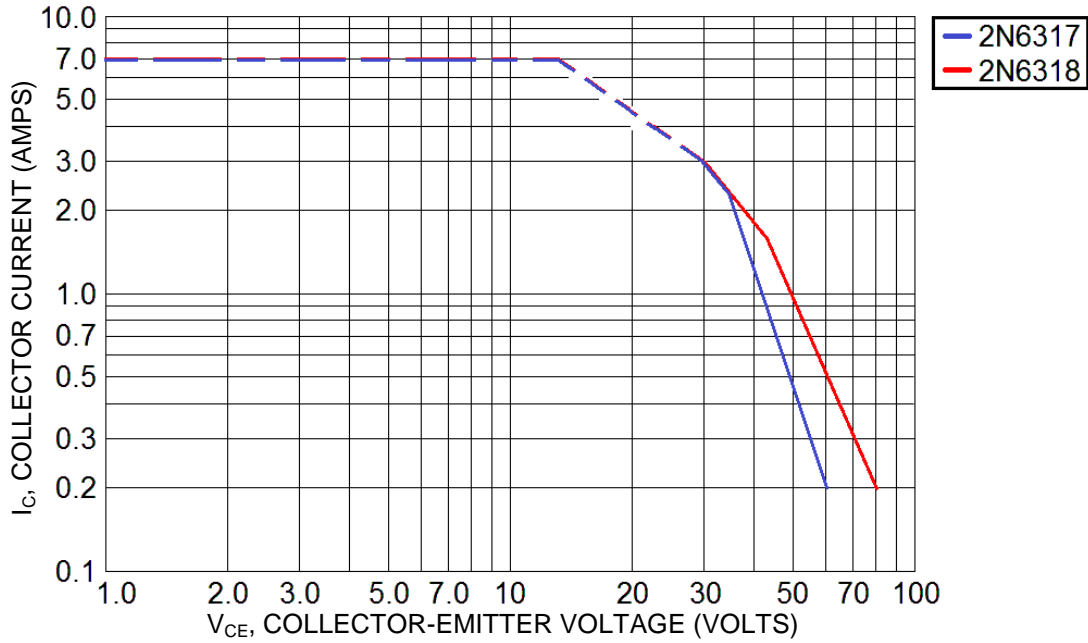
**DYNAMIC CHARACTERISTICS**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $V_{CE} = 10 V, I_C = 0.25 A, f = 1 MHz$	$ h_{fe} $	4		
Common Base Output $V_{CB} = 10 V, I_E = 0 A, f = 1 MHz$	$C_{ob}$		300	pF
Common Emitter Small-Signal Short-Circuit Forward Current Trans-Ratio $V_{CE} = 4 V, I_C = 0.5 A, f = 1 kHz$	$h_{fe}$	20		

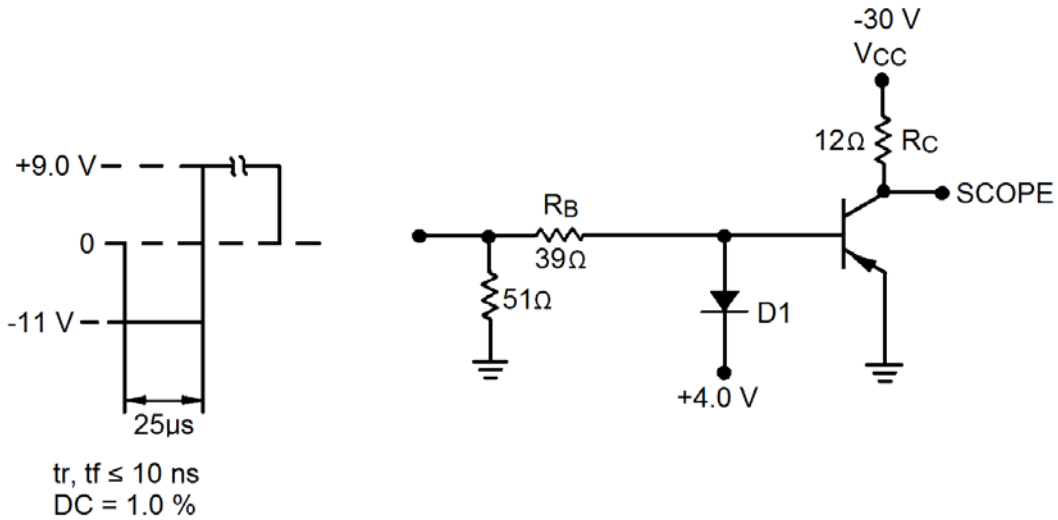
**SWITCHING CHARACTERISTICS**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Rise time $V_{CC} = 30 V, I_C = 25 A, I_{B1} = I_{B2} = 0.25 A$ (see <a href="#">figure 2</a> )	$t_r$		0.7	$\mu s$
Storage time $V_{CC} = 30 V, I_C = 25 A, I_{B1} = I_{B2} = 0.25 A$ (see <a href="#">figure 2</a> )	$t_s$		1.0	$\mu s$
Fall time $V_{CC} = 30 V, I_C = 25 A, I_{B1} = I_{B2} = 0.25 A$ (see <a href="#">figure 2</a> )	$t_f$		0.8	$\mu s$

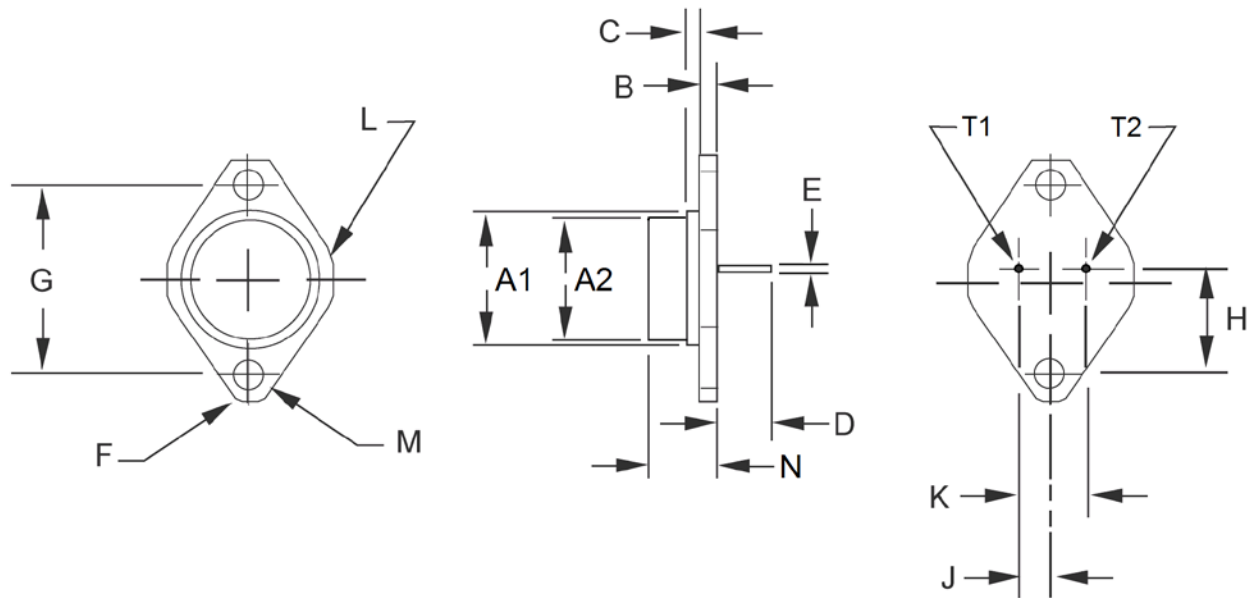
GRAPHS



**Figure 1**  
Safe Operating Area ( $T_C = 25\text{ }^\circ\text{C}$ )



**Figure 2**  
Switching Times Test Circuit

**PACKAGE DIMENSIONS**


DIM	INCH		MILLIMETERS	
	MIN	MAX	MIN	MAX
A1	.470	.500	11.94	12.70
A2	-	.620	-	15.75
B	.050	.075	1.27	1.91
C	-	.050	-	1.27
D	.360	-	9.14	-
E	.028	.034	0.71	0.86
F	.145 radius		3.68 radius	
G	.958	.962	24.33	24.43
H	.570	.590	14.48	14.99
J	.093	.107	2.36	2.72
K	.190	.210	4.83	5.33
L	.350 radius		8.89 radius	
M	.142	.152	3.61	3.86
N	.250	.340	6.35	8.64
T1	Base			
T2	Emitter			
Case	Collector			